NSN 5961-01-118-5823

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View Online at https://aerobasegroup.com/nsn/5961-01-118-5823 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **End Application:** 5810-01-017-0008 13643 **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 collector to base voltage/static/emitter open and 100.0 collector to emitter voltage/static/base open and 7.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** Between 4.00 amperes source cutoff current and 6.00 amperes source cutoff current **Power Rating Per Characteristic:** 150.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnp **Terminal Type And Quantity:** 1 case and 2 pin **Specification Data:** 80131-release6334 professional/industrial association specification Shelf Life:

No

N/a

Unit Of Measure:

Demilitarization:

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